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MOS INTEGRATED CIRCUIT μ PD75P3216

4-BIT SINGLE-CHIP MICROCONTROLLER

The μ PD75P3216 replaces the μ PD753208's internal mask ROM with a one-time PROM, and features expanded ROM capacity.

Because the μ PD75P3216 supports programming by users, it is suitable for use in prototype testing for system development using the μ PD753204, 753206, or 753208, and for use in small-lot production.

The functions are explained in detail in the following user's manual. Be sure to read this manual when designing your system.

 μ PD753208 User's Manual: U10158E

FEATURES

- Compatible with μPD753208
- Memory capacity:

PROM: 16384 × 8 bits
 RAM: 512 × 4 bits

- Can operate in same power supply voltage range as the mask version μ PD753208
 - $V_{DD} = 1.8 \text{ to } 5.5 \text{ V}$
- LCD controller/driver

ORDERING INFORMATION

Part Number	Package				
μPD75P3216GT	48-pin plastic shrink SOP (375 mil, 0.65-mm pitch)				
μPD75P3216GT-A	48-pin plastic shrink SOP (375 mil, 0.65-mm pitch)				

Caution Mask-option pull-up resistors are not provided in this device.

Remark Products with "-A" at the end of the part number are lead-free products.

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FUNCTION OUTLINE

Parameter			Function				
Instruction	n execution tim	ne		 0.95, 1.91, 3.81, 15.3 μs (@ 4.19-MHz operation with system clock) 0.67, 1.33, 2.67, 10.7 μs (@ 6.0-MHz operation with system clock) 			
Internal memory PROM			163	884 × 8 bits			
		RAM	512	2 × 4 bits			
General-p	ourpose registe	er	• 4	-bit operation: 8×4 ba	nks		
			• 8	3-bit operation: 4×4 ba	nks		
Input/	CMOS input		6	Connecting on-chip pu	II-up resistors can be specified by software: 5		
output port	CMOS input/	output	20	Connecting on-chip pu Also used for segment	II-up resistors can be specified by software: 20 pins: 8		
	N-ch open-di	rain I/O	4	13-V withstand			
	Total		30				
LCD cont	LCD controller/driver			 Segment selection: 4/8/12 segments (can be changed to CMOS input/output port in 4-time units; max. 8) Display mode selection: Static 1/2 duty (1/2 bias) 1/3 duty (1/2 bias) 1/3 duty (1/3 bias) 1/4 duty (1/3 bias) 			
Timer	Timer			hannels 3-bit timer/event counter: 3-bit timer counter: 2 ch generator, timer with gat 3asic interval timer/watcl Vatch timer: 1 channel	annels (can be used as the 16-bit timer counter, carrier		
Serial inte	Serial interface			 3-wire serial I/O mode MSB or LSB can be selected for transferring first bit 2-wire serial I/O mode SBI mode 			
Bit seque	ntial buffer (BS	SB)	16	bits			
Clock out	put (PCL)		 Φ, 524, 262, 65.5 kHz (@ 4.19-MHz operation with system clock) Φ, 750, 375, 93.8 kHz (@ 6.0-MHz operation with system clock) 				
Buzzer ou	Buzzer output (BUZ)		 2, 4, 32 kHz (@ 4.19-MHz operation with system clock) 2.93, 5.86, 46.9 kHz (@ 6.0-MHz with system clock) 				
Vectored	interrupts		Ext	ernal: 2, Internal: 5			
Test inpu	t		External: 1, Internal: 1				
System c	lock oscillator		Cei	ramic or crystal oscillato	r for system clock oscillation		
Standby f	unction		ST	OP/HALT mode			
Power su	pply voltage		VDE	V _{DD} = 1.8 to 5.5 V			
Package			48-pin plastic shrink SOP (375 mil, 0.65-mm pitch)				

2



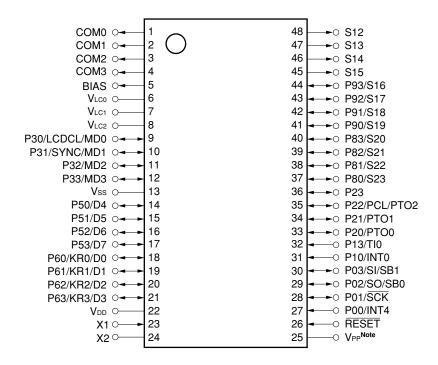
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1. PIN CONFIGURATION (Top View)

- 48-pin plastic shrink SOP (375 mil, 0.65-mm pitch) μ PD75P3216GT
- \star μ PD75P3216GT-A



Note Be sure to connect VPP to VDD directly in normal operation mode.

PIN IDENTIFICATIONS

PCL	: Programmable Clock

BIAS : LCD Power Supply Bias Control PTO0-PTO2 : Programmable Timer Output 0 to 2

BUZ : Buzzer Clock RESET : Reset Input

COM0-COM3: Common Output 0 to 3 S12-S23: Segment Output 12 to 23

D0-D7 : Data Bus 0 to 7 SB0, SB1 : Serial Bus 0, 1
INT0, INT4 : External Vectored Interrupt 0, 4 SCK : Serial Clock
KR0-KR3 : Key Return 0 to 3 SI : Serial Input
I CDCI : I CD Clock SO : Serial Output

LCDCL : LCD Clock SO : Serial Output

MD0-MD3 : Mode Selection 0 to 3 SYNC : LCD Synchronization P00-P03 : Port0 TI0 : Timer Input 0

P10, P13 : Port1 V_{DD} : Positive Power Supply

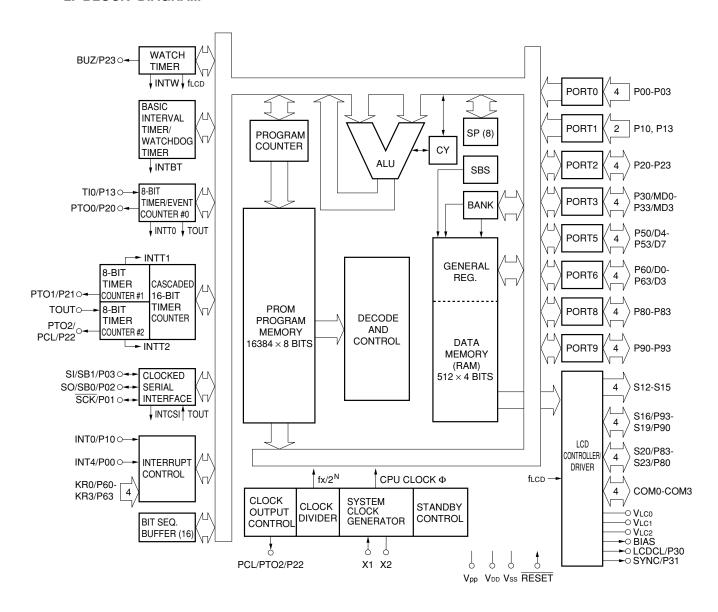
P50-P53 : Port5 Vss : Ground

P60-P63 : Port6 X1, X2 : System Clock Oscillation 1, 2

P80-P83 : Port8 P90-P93 : Port9



2. BLOCK DIAGRAM





3. PIN FUNCTIONS

3.1 Port Pins

	Pin Name	I/O	Shared by	Function 8-bit Status I/O After Reset		Status After Reset	I/O Circuit Type ^{Note 1}
	P00	Input	INT4	This is a 4-bit input port (PORT0).	×	Input	
	P01	I/O	SCK	P01 to P03 are 3-bit pins for which an internal			<f>-A</f>
	P02	I/O	SO/SB0	pull-up resistor can be connected by software.			<f>-B</f>
	P03	I/O	SI/SB1				<m>-C</m>
	P10	Input	INT0	This is a 1-bit input port (PORT1). These are 1-bit pins for which an internal pull-up	×	Input	-C
	P13		TI0	resistor can be connected by software. P10/INT0 can select noise elimination circuit.			
	P20	I/O	PTO0	This is a 4-bit I/O port (PORT2).	×	Input	E-B
	P21		PTO1	These are 4-bit pins for which an internal pull-up			
	P22		PCL/PTO2	resistor can be connected by software.			
	P23		BUZ				
	P30	I/O	LCDCL/MD0	This is a programmable 4-bit I/O port (PORT3).	×	Input	E-B
	P31		SYNC/MD1	Input and output in single-bit units can be specified.			
	P32		MD2	When set for 4-bit units, an internal pull-up resistor can be connected by software.			
	P33		MD3	,			
*	P50Note 2	I/O	D4	This is an N-ch open-drain 4-bit I/O port (PORT5).	×	High	M-E
	P51 Note 2		D5	When set to open-drain, voltage is 13 V.		impedance	
	P52Note 2		D6	Also functions as data I/O pin (upper 4 bits) for program memory (PROM) write/verify.			
	P53Note 2		D7				
*	P60	I/O	KR0/D0	This is a programmable 4-bit I/O port (PORT6). Input and output in single-bit units can be specified.	×	Input	<f>-A</f>
	P61		KR1/D1	When set for 4-bit units, an internal pull-up resistor			
	P62		KR2/D2	can be connected by software. Also functions as data I/O pin (lower 4 bits) for			
	P63		KR3/D3	program memory (PROM) write/verify.			
	P80	I/O	S23	This is a 4-bit I/O port (PORT8).	0	Input	Н
	P81		S22	When set for 4-bit units, an internal pull-up resistor			
	P82		S21	can be connected by software.			
	P83		S20				
	P90	I/O	S19	This is a programmable 4-bit I/O port (PORT9).		Input	Н
	P91		S18	When set for 4-bit units, an internal pull-up resistor			
	P92		S17	can be connected by software.			
	P93	1	S16				

Notes 1. Circuit types enclosed in brackets indicate Schmitt trigger circuits.

2. Low level input current leakage increases when input instructions or bit manipulation instructions are executed.

3.2 Non-port Pins

Pin Name	I/O	Shared by	Function	Status After Reset	I/O Circuit Type ^{Note 1}
TI0	Input	P13	External event pulse input to timer/event counter	Input	-C
PTO0	Output	P20	Timer/event counter output	Input	E-B
PTO1		P21	Timer counter output		
PTO2		P22/PCL			
PCL		P22/PTO2	Clock output		
BUZ		P23	Any frequency output (for buzzer or system clock trimming)		
SCK	I/O	P01	Serial clock I/O	Input	<f>-A</f>
SO/SB0		P02	Serial data output Serial data bus I/O		<f>-B</f>
SI/SB1		P03	Serial data input Serial data bus I/O		<m>-C</m>
INT4	Input	P00	Edge detection vectored interrupt input (detecting both rising and falling edges)	Input	
INT0	Input	P10	Edge detection vectored interrupt input (detected edge is selectable). INTO/P10 can select noise elimination circuit is selectable	Input	-C
KR0 to KR3	Input	P60/D0-P63/D3	Falling edge detection testable input	Input	<f>-A</f>
X1	Input	_	Ceramic/crystal oscillation circuit connection for system clock. If using an external clock, input to X1 and input	_	_
X2	_		inverted phase to X2.		
RESET	Input	_	System reset input		
MD0 to MD3	Input	P30 to P33	Mode selection for program memory (PROM) write/verify	Input	<f>-A</f>
D0 to D3	I/O	P60/KR0-P63/KR3	Data bus pin for program memory (PROM) write/verify.	Input	<f>-A</f>
D4 to D7		P50 to P53			M-E
V _{PP}	_	_	Programmable power supply voltage for program memory (PROM) write/verify. For normal operation, connect directly to VDD. Apply +12.5 V for PROM write/verify.	_	_
V _{DD}	_	_	Positive power supply	_	_
Vss	_	_	Ground	_	_
S12 to S15	Output	_	Segment signal output	Note 2	G-A
S16 to S19	Output	P93 to P90	Segment signal output	Input	Н
S20 to S23		P83 to P80			
COM0 to COM3	Output	_	Common signal output	Note 2	G-B
VLC0 to VLC2	_	_	Power source for LCD drive	_	_
BIAS	Output	_	Output for external split resistor cut	Note 3	_
LCDCLNote 4	Output	P30/MD0	Clock output for driving external expansion driver	Input	E-B
SYNCNote 4]	P31/MD1	Clock output for synchronization of external expansion driver	1	

Notes 1. Circuit types enclosed in brackets indicate Schmitt trigger circuits.

2. The V_{LCX} (X = 0, 1, 2) shown below are selected as the input source for the display outputs. S12 to S15: V_{LC1} , COM1 to COM2: V_{LC2} , COM3: V_{LC0}

3. When the split resistor is incorporated : Low level When the split resistor is not incorporated : High impedance

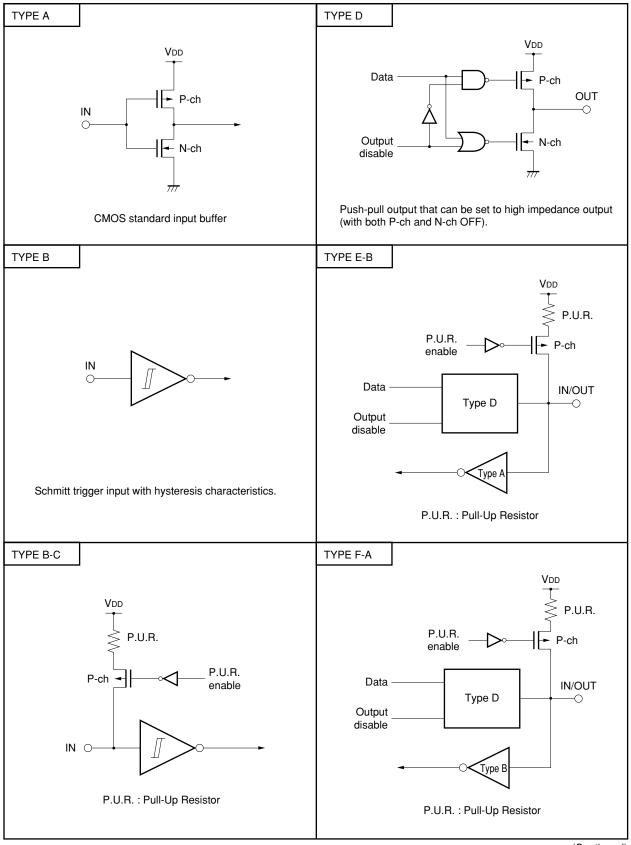
4. These pins are provided for future system expansion. Currently, only P30 and P31 are used.

*



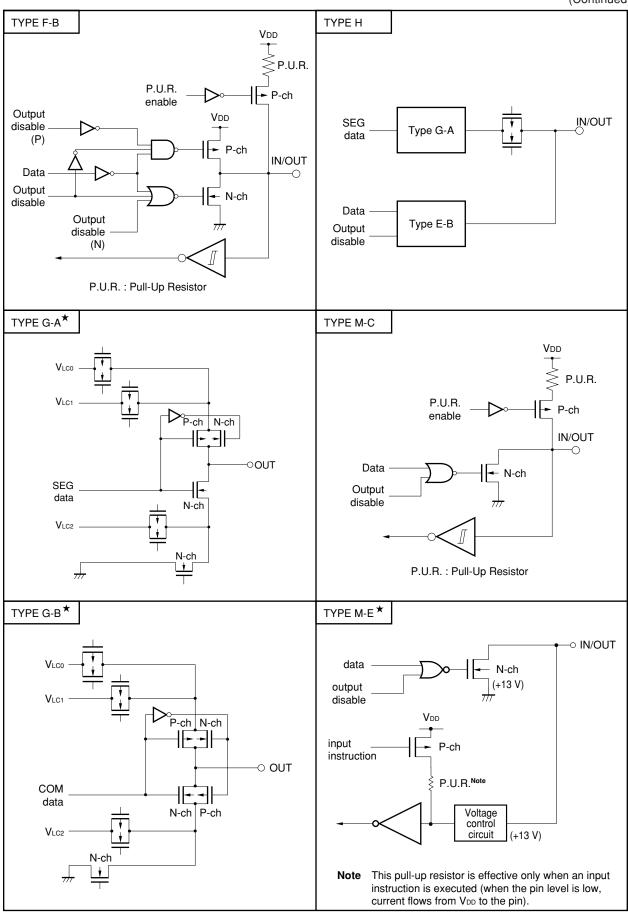
3.3 Equivalent Circuits for Pins

The equivalent circuits for the μ PD75P3216's pins are shown in abbreviated form below.



(Continued)

(Continued)





★ 3.4 Recommended Connection of Unused Pins

Pin	Recommended Connection
P00/INT4	Connect to Vss or VDD
P01/SCK	Connect to Vss or VDD through a resistor individually
P02/SO/SB0	
P03/SI/SB1	Connect to Vss
P10/INT0	Connect to Vss or VDD
P13/TI0	
P20/PTO0	Input status : connect to Vss or VDD through a resistor individually
P21/PTO1	Output status: open
P22/PTO2/PCL	
P23/BUZ	
P30/MD0/LCDCL	
P31/MD1/SYNC	
P32/MD2	
P33/MD3	
P50/D4 to P53/D7	Connect to Vss
P60/KR0/D0 to P63/KR3/D3	Input status : connect to Vss or VDD through a resistor individually
	Output status: open
S12 to S15	Open
COM0 to COM3	
S16/P93 to S19/P90	Input status : connect to Vss or VDD through a resistor individually
S20/P83 to S23/P80	Output status: open
VLC0 to VLC2	Connect to Vss
BIAS	Connect to Vss only when VLco to VLc2 are all not used. In other cases, leave open.
VPP	Be sure to connect VDD directly.

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4. Mk I AND Mk II MODE SELECTION FUNCTION

Setting a stack bank selection (SBS) register for the μ PD75P3216 enables the program memory to be switched between Mk I mode and Mk II mode. This function is applicable when using the μ PD75P3216 to evaluate the μ PD753204, 753206, or 753208.

When the SBS bit 3 is set to 1: sets Mk I mode (supports Mk I mode for μ PD753204, 753206, and 753208) When the SBS bit 3 is set to 0: sets Mk II mode (supports Mk II mode for μ PD753204, 753206, and 753208)

4.1 Difference between Mk I Mode and Mk II Mode

Table 4-1 lists points of difference between the Mk I mode and the Mk II mode for the μ PD75P3216.

Table 4-1. Difference between Mk I Mode and Mk II Mode

Item		Mk I Mode	Mk II Mode	
Program counte	er	PC13-0		
Program memo	ory (bytes)	16384		
Data memory (bits)	512 × 4		
Stack	Stack bank	Selectable via memory banks 0, 1		
	No. of stack bytes	2 bytes	3 bytes	
Instruction	BRA !addr1 instruction	None	Provided	
	CALLA !addr1 instruction			
Instruction	CALL laddr instruction	3 machine cycles	4 machine cycles	
execution time	CALLF !faddr instruction	2 machine cycles	3 machine cycles	
Supported mas	k ROMs	When set to Mk I mode: When set to Mk II mode: μPD753204, 753206, and 753208 μPD753204, 753206, and 75320		

★ Caution The Mk II mode supports a program area which exceeds 16K bytes in the 75X and 75XL series. This mode enhances the software compatibility with products which have more than 16K bytes. When the Mk II mode is selected, the number of stack bytes used in execution of a subroutine call instruction increases by 1 per stack for the usable area compared to the Mk I mode. Furthermore, when a CALL !addr, or CALLF !faddr instruction is used, each instruction takes another machine cycle. Therefore, when more importance is attached to RAM utilization or throughput than software compatibility, use the Mk I mode.

Data Sheet U10241EJ1V1DS 11

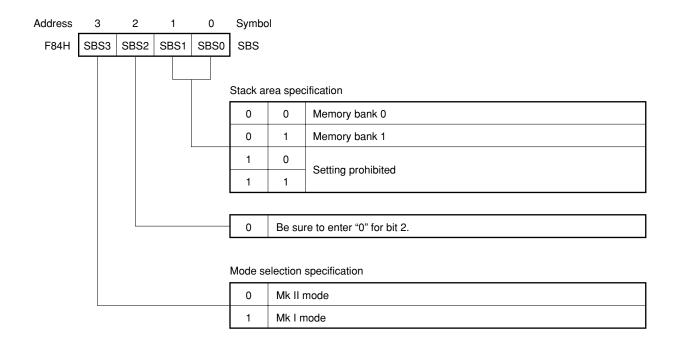
4.2 Setting of Stack Bank Selection (SBS) Register

Use the stack bank selection register to switch between Mk I mode and Mk II mode. Figure 4-1 shows the format for doing this.

The stack bank selection register is set using a 4-bit memory manipulation instruction. When using the Mk I mode, be sure to initialize the stack bank selection register to 100XB^{Note} at the beginning of the program. When using the Mk II mode, be sure to initialize it to 000XB^{Note}.

Note Set the desired value for X.

Figure 4-1. Format of Stack Bank Selection Register



- Cautions 1. SBS3 is set to "1" after RESET input, and consequently the CPU operates in Mk I mode. When using instructions for Mk II mode, set SBS3 to "0" and set Mk II mode before using the instructions.
 - 2. When using Mk II mode, execute a subroutine call instruction and an interrupt instruction after RESET input and after setting the stack bank selection register.



5. DIFFERENCES BETWEEN μ PD75P3216 AND μ PD753204, 753206, AND 753208

The μ PD75P3216 replaces the internal mask ROM in the μ PD753204, 753206, and 753208 with a one-time PROM and features expanded ROM capacity. The μ PD75P3216's Mk I mode supports the Mk I mode in the μ PD753204, 753206, and 753208 and the μ PD75P3216's Mk II mode supports the Mk II mode in the μ PD753204, 753206, and 753208.

Table 5-1 lists differences among the μ PD75P3216 and the μ PD753204, 753206, and 753208. Be sure to check the differences among these products before using them with PROMs for debugging or prototype testing of application systems or, later, when using them with a mask ROM for full-scale production.

For details on the CPU functions and internal hardware, refer to µPD753208 User's Manual (U10158E).

Table 5-1. Differences between μ PD75P3216 and μ PD753204, 753206, and 753208

	Item	μPD753204	μPD753206	μPD753208	μPD75P3216
Program counter		12 bits	13 bits	13 bits	
Program memory (bytes)		Mask ROM 4096	Mask ROM 6144	Mask ROM 8192	One-time PROM 16384
Data memory (x 4	l bits)	512			
Mask options	Pull-up resistor for port 5	Yes (specifiable) No (off chip		No (off chip)	
	Waiting time in RESET	Yes (selectable fro	No (Fixed to 2 ¹⁵ /fx ms)		
Pin configuration	Pin 9 to 12	P30 to P33			P30/MD0-P33/MD3
	Pin 14 to 17	P50 to P53	P50/D4-P53/D7		
	Pin 18 to 20	P60/KR0 to P63/KR3			P60/KR0/D0- P63/KR3/D3
	Pin 25	IC	VPP		
Other		Noise resistance at mask layouts.	e resistance and noise radiation may differ due to the different circuit sizes at k layouts.		

Note $2^{17}/fx = 21.8 \text{ ms } (@6.0 \text{ MHz}), 31.3 \text{ ms } (@4.19 \text{ MHz})$

 $2^{15}/fx = 5.46 \text{ ms } (@6.0 \text{ MHz}), 7.81 \text{ ms } (@4.19 \text{ MHz})$

Caution Noise resistance and noise radiation are different in PROM and mask ROMs. In transferring to mask ROM versions from the PROM version in a process between prototype development and full production, be sure to fully evaluate the mask ROM version's CS (not ES).

*



6. MEMORY CONFIGURATION

7 5 6 0 0000H MBE RBE Internal reset start address (upper 6 bits) Internal reset start address (lower 8 bits) 0002H **MBE RBE** INTBT/INT4 start address (upper 6 bits) **CALLF** INTBT/INT4 start address (lower 8 bits) !faddr instruction 0004H MBE RBE INTO start address (upper 6 bits) entry address INTO start address (lower 8 bits) 0006H **BRCB** !caddr instruction 0008H MBE **RBE** INTCSI start address (upper 6 bits) branch address INTCSI start address (lower 8 bits) Branch addresses for the following instructions RBE 000AH MBE INTT0 start address (upper 6 bits) • BR !addr · CALL !addr INTT0 start address (lower 8 bits) • BRA !addr1 Note CALLA !addr1 Note **RBE** 000CH MBE INTT1/INTT2 start address (upper 6 bits) MOVT BCDE INTT1/INTT2 start address (lower 8 bits) MOVT BCXA Branch/call address 0020H by GETI Reference table for GETI instruction 007FH **BR** \$addr instruction 0080H relative branch address (-15 to -1)+2 to +16) 07FFH 0800H 0FFFH 1000H BRCB !caddr instruction branch address 1FFFH 2000H BRCB !caddr instruction branch address 2FFFH 3000H BRCB !caddr instruction branch address 3FFFH

Figure 6-1. Program Memory Map

Note Can be used only in Mk II mode.

Remark For instructions other than those noted above, the BR PCDE and BR PCXA instructions can be used to branch to addresses with changes in the PC's lower 8 bits only.

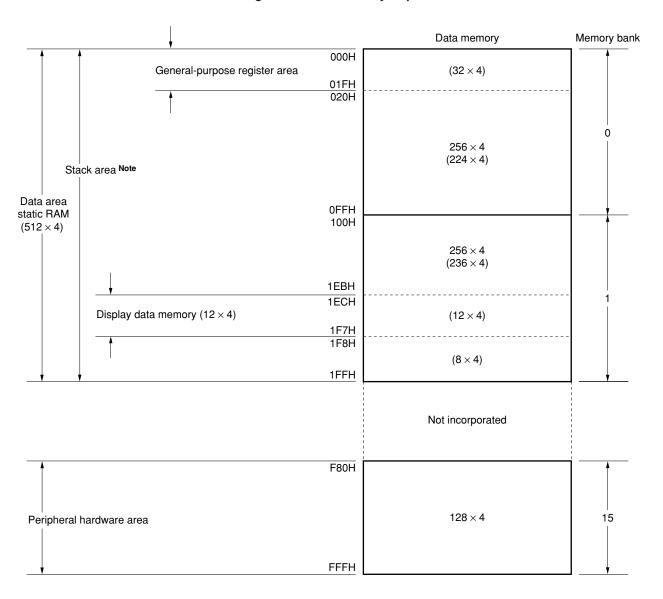


Figure 6-2. Data Memory Map

Note Memory bank 0 or 1 can be selected as the stack area.

7. INSTRUCTION SET

(1) Representation and coding formats for operands

In the instruction's operand area, use the following coding format to describe operands corresponding to the instruction's operand representations (for further description, refer to RA75X Assembler Package User's Manual –Language (EEU-1343)). When there are several codes, select and use just one. Codes that consist of upper-case letters and + or – symbols are key words that should be entered as they are.

For immediate data, enter an appropriate numerical value or label.

Enter register flag symbols as label descriptors instead of mem, fmem, pmem, bit, etc. (for further description, refer to μ PD753208 User's Manual (U10158E)). The number of labels that can be entered for fmem and pmem are restricted.

Representation	Coding Format
reg	X, A, B, C, D, E, H, L
reg1	X, B, C, D, E, H, L
rp	XA, BC, DE, HL
rp1	BC, DE, HL
rp2	BC, DE
rp'	XA, BC, DE, HL, XA', BC', DE', HL'
rp'1	BC, DE, HL, XA', BC', DE', HL'
rpa	HL, HL+, HL-, DE, DL
rpa1	DE, DL
n4	4-bit immediate data or label
n8	8-bit immediate data or label
mem	8-bit immediate data or label ^{Note}
bit	2-bit immediate data or label
fmem	FB0H to FBFH, FF0H to FFFH immediate data or label
pmem	FC0H to FFFH immediate data or label
addr	0000H to 3FFFH immediate data or label
addr1	0000H to 3FFFH immediate data or label (Mk II mode only)
caddr	12-bit immediate data or label
faddr	11-bit immediate data or label
taddr	20H to 7FH immediate data (however, bit0 = 0) or label
PORTn	PORT0 to PORT3, PORT5, PORT6, PORT8, PORT9
IEXXX	IEBT, IECSI, IET0, IET1, IET2, IE0, IE2, IE4, IEW
RBn	RB0 to RB3
MBn	MB0, MB1, MB15

Note When processing 8-bit data, only even-numbered addresses can be specified.



(2) Operation legend

A : A register; 4-bit accumulator

B : B register
C : C register
D : D register
E : E register
H : H register
L : L register
X : X register

XA : Register pair (XA); 8-bit accumulator

BC : Register pair (BC)
DE : Register pair (DE)
HL : Register pair (HL)

XA' : Expansion register pair (XA')
BC' : Expansion register pair (BC')
DE' : Expansion register pair (DE')
HL' : Expansion register pair (HL')

PC : Program counter SP : Stack pointer

CY : Carry flag; bit accumulator
PSW : Program status word

MBE : Memory bank enable flag

RBE : Register bank enable flag

PORTn : Port n (n = 0 to 3, 5, 6, 8, 9)

IME : Interrupt master enable flag

IPS : Interrupt priority selection register

IEXXX : Interrupt enable flag

RBS : Register bank selection register
MBS : Memory bank selection register
PCC : Processor clock control register
. : Delimiter for address and bit

(XX) : Addressed dataXXH : Hexadecimal data



(3) Description of symbols used in addressing area

	MB = MBE • MBS	A
*1	MBS = 0, 1, 15	
*2	MB = 0	
	MBE = 0 : MB = 0 (000H to 07FH)	
**	MB = 15 (F80H to FFFH)	Data memory addressing
*3	MBE = 1 : MB = MBS	
	MBS = 0, 1, 15	
*4	MB = 15, fmem = FB0H to FBFH, FF0H to FFFH	
*5	MB = 15, pmem = FC0H to FFFH	
*6	addr = 0000H to 3FFFH	•
*7	addr, addr1 = (Current PC) - 15 to (Current PC) - 1	1
'	(Current PC) +2 to (Current PC) +16	
	caddr = 0000H to 0FFFH (PC13, 12 = 00B) or	
	1000H to 1FFFH (PC13, 12 = 01B) or	Program memory
*8	2000H to 2FFFH (PC13, 12 = 10B) or	addressing
	3000H to 3FFFH (PC13, 12 = 11B)	
*9	faddr = 0000H to 07FFH	
*10	taddr = 0020H to 007FH	
*11	addr1 = 0000H to 3FFFH (Mk II mode only)	_

Remarks 1. MB indicates access-enabled memory banks.

- 2. In area *2, MB = 0 for both MBE and MBS.
- 3. In areas *4 and *5, MB = 15 for both MBE and MBS.
- 4. Areas *6 to *11 indicate corresponding address-enabled areas.

(4) Description of machine cycles

S indicates the number of machine cycles required for skipping of skip-specified instructions. The value of S varies as shown below.

- Skipped instruction is 1-byte or 2-byte instruction .. S = 1
- Skipped instruction is 3-byte instruction Note S = 2

Note 3-byte instructions: BR !addr, BRA !addr1, CALL !addr, and CALLA !addr1

Caution The GETI instruction is skipped for one machine cycle.

One machine cycle equals one cycle (= tCY) of the CPU clock F. Use the PCC setting to select among four cycle times.



Instruction Group	Mnemonic	Operand	No. of Bytes	Machine Cycle	Operation	Addressing Area	Skip Condition
Transfer	MOV	A, #n4	1	1	A←n4		String-effect A
		reg1, #n4	2	2	reg1←n4		
		XA, #n8	2	2	XA←n8		String-effect A
		HL, #n8	2	2	HL←n8		String-effect B
		rp2, #n8	2	2	rp2←n8		
		A, @HL	1	1	A←(HL)	*1	
		A, @HL+	1	2+S	A←(HL), then L←L+1	*1	L=0
		A, @HL-	1	2+S	A←(HL), then L←L-1	*1	L=FH
		A, @rpa1	1	1	A←(rpa1)	*2	
		XA, @HL	2	2	XA←(HL)	*1	
		@HL, A	1	1	(HL)←A	*1	
		@HL, XA	2	2	(HL)←XA	*1	
		A, mem	2	2	A←(mem)	*3	
		XA, mem	2	2	XA←(mem)	*3	
		mem, A	2	2	(mem)←A	*3	
		mem, XA	2	2	(mem)←XA	*3	
		A, reg	2	2	A←reg		
		XA, rp'	2	2	XA←rp'		
		reg1, A	2	2	reg1←A		
		rp'1, XA	2	2	rp'1←XA		
	XCH	A, @HL	1	1	A↔(HL)	*1	
		A, @HL+	1	2+S	A↔(HL), then L←L+1	*1	L=0
		A, @HL-	1	2+S	A↔(HL), then L←L-1	*1	L=FH
		A, @rpa1	1	1	A↔(rpa1)	*2	
		XA, @HL	2	2	XA↔(HL)	*1	
		A, mem	2	2	A↔(mem)	*3	
		XA, mem	2	2	XA↔(mem)	*3	
		A, reg1	1	1	A⇔reg1		
		XA, rp'	2	2	XA↔rp'		
Table	MOVT	XA, @PCDE	1	3	XA←(PC13-8+DE)ROM		
reference		XA, @PCXA	1	3	XA←(PC13-8+XA)ROM		
		XA, @BCDENote	1	3	XA←(B2-0+BCDE)ROM	*6	
		XA, @BCXA ^{Note}	1	3	XA←(B2-0+BCXA)ROM	*6	

Note Only the lower 2 bits in the B register are valid.



Instruction Group	Mnemonic	Operand	No. of Bytes	Machine Cycle	Operation	Addressing Area	Skip Condition
Bit transfer	MOV1	CY, fmem.bit	2	2	CY←(fmem.bit)	*4	
		CY, pmem.@L	2	2	CY←(pmem7-2+L3-2.bit(L1-0))	*5	
		CY, @H+mem.bit	2	2	CY←(H+mem₃-o.bit)	*1	
		fmem.bit, CY	2	2	(fmem.bit)←CY	*4	
		pmem.@L, CY	2	2	(pmem7-2+L3-2.bit(L1-0))←CY	*5	
		@H+mem.bit, CY	2	2	(H+mem₃-o.bit)←CY	*1	
Arithmetic	ADDS	A, #n4	1	1+S	A←A+n4		carry
		XA, #n8	2	2+S	XA←XA+n8		carry
		A, @HL	1	1+S	A←A+(HL)	*1	carry
		XA, rp'	2	2+S	XA←XA+rp'		carry
		rp'1, XA	2	2+S	rp'1←rp'1+XA		carry
	ADDC	A, @HL	1	1	A, CY←A+(HL)+CY	*1	
		XA, rp'	2	2	XA, CY←XA+rp'+CY		
		rp'1, XA	2	2	rp'1, CY←rp'1+XA+CY		
	SUBS	A, @HL	1	1+S	A←A−(HL)	*1	borrow
		XA, rp'	2	2+S	XA←XA–rp'		borrow
5		rp'1, XA	2	2+S	rp'1←rp'1−XA		borrow
	SUBC	A, @HL	1	1	A, CY←A−(HL)−CY	*1	
		XA, rp'	2	2	XA, CY←XA–rp'–CY		
		rp'1, XA	2	2	rp'1, CY←rp'1–XA–CY		
	AND	A, #n4	2	2	A←A∧n4		
		A, @HL	1	1	$A \leftarrow A \land (HL)$	*1	
		XA, rp'	2	2	XA←XA∧rp'		
		rp'1, XA	2	2	rp'1←rp'1∧XA		
	OR	A, #n4	2	2	A←A∨n4		
		A, @HL	1	1	$A \leftarrow A \lor (HL)$	*1	
		XA, rp'	2	2	XA←XA∨rp'		
		rp'1, XA	2	2	rp'1←rp'1∨XA		
	XOR	A, #n4	2	2	A←A∀n4		
		A, @HL	1	1	$A \leftarrow A \forall (HL)$	*1	
		XA, rp'	2	2	XA←XA∀rp'		
		rp'1, XA	2	2	rp'1←rp'1∀XA		
Accumulator	RORC	А	1	1	CY←A0, A3←CY, An-1←An		
manipulation	NOT	А	2	2	$A \leftarrow \overline{A}$		
ncrement/	INCS	reg	1	1+S	reg←reg+1		reg=0
decrement		rp1	1	1+S	rp1←rp1+1		rp1=00H
		@HL	2	2+S	(HL)←(HL)+1	*1	(HL)=0
		mem	2	2+S	(mem)←(mem)+1	*3	(mem)=0
	DECS	reg	1	1+S	reg←reg–1		reg=FH
		rp'	2	2+S	rp'←rp'–1		rp'=FFH



Instruction Group	Mnemonic	Operand	No. of Bytes	Machine Cycle	Operation	Addressing Area	Skip Condition
Comparison	SKE	reg, #n4	2	2+S	Skip if reg=n4		reg=n4
		@HL, #n4	2	2+S	Skip if(HL)=n4	*1	(HL)=n4
		A, @HL	1	1+S	Skip if A=(HL)	*1	A=(HL)
		XA, @HL	2	2+S	Skip if XA=(HL)	*1	XA=(HL)
		A, reg	2	2+S	Skip if A=reg		A=reg
		XA, rp'	2	2+S	Skip if XA=rp'		XA=rp'
Carry flag	SET1	CY	1	1	CY←1		
manipulation	CLR1	CY	1	1	CY←0		
	SKT	CY	1	1+S	Skip if CY=1		CY=1
	NOT1	CY	1	1	CY←CY		
Memory bit	SET1	mem.bit	2	2	(mem.bit)←1	*3	
manipulation		fmem.bit	2	2	(fmem.bit)←1	*4	
		pmem.@L	2	2	(pmem7-2+L3-2.bit(L1-0))←1	*5	
		@H+mem.bit	2	2	(H+mem₃-o.bit)←1	*1	
	CLR1	mem.bit	2	2	(mem.bit)←0	*3	
		fmem.bit	2	2	(fmem.bit)←0	*4	
		pmem.@L	2	2	(pmem7-2+L3-2.bit(L1-0))←0	*5	
		@H+mem.bit	2	2	(H+mem₃-o.bit)←0	*1	
	SKT	mem.bit	2	2+S	Skip if(mem.bit)=1	*3	(mem.bit)=1
		fmem.bit	2	2+S	Skip if(fmem.bit)=1	*4	(fmem.bit)=1
		pmem.@L	2	2+S	Skip if(pmem7-2+L3-2.bit(L1-0))=1	*5	(pmem.@L)=1
		@H+mem.bit	2	2+S	Skip if(H+mem3-0.bit)=1	*1	(@H+mem.bit)=1
	SKF	mem.bit	2	2+S	Skip if(mem.bit)=0	*3	(mem.bit)=0
		fmem.bit	2	2+S	Skip if(fmem.bit)=0	*4	(fmem.bit)=0
		pmem.@L	2	2+S	Skip if(pmem7-2+L3-2.bit(L1-0))=0	*5	(pmem.@L)=0
		@H+mem.bit	2	2+S	Skip if(H+mem3-0.bit)=0	*1	(@H+mem.bit)=0
	SKTCLR	fmem.bit	2	2+S	Skip if(fmem.bit)=1 and clear	*4	(fmem.bit)=1
		pmem.@L	2	2+S	Skip if(pmem7-2+L3-2.bit (L1-0))=1 and clear	*5	(pmem.@L)=1
		@H+mem.bit	2	2+S	Skip if(H+mem ₃₋₀ .bit)=1 and clear	*1	(@H+mem.bit)=1
	AND1	CY, fmem.bit	2	2	CY←CY∧(fmem.bit)	*4	
		CY, pmem.@L	2	2	CY←CY∧(pmem7-2+L3-2.bit(L1-0))	*5	
		CY, @H+mem.bit	2	2	CY←CY∧(H+mem₃-o.bit)	*1	
	OR1	CY, fmem.bit	2	2	CY←CY√(fmem.bit)	*4	
		CY, pmem.@L	2	2	CY←CY√(pmem7-2+L3-2.bit(L1-0))	*5	
		CY, @H+mem.bit	2	2	CY←CY√(H+mem3-0.bit)	*1	
	XOR1	CY, fmem.bit	2	2	CY←CY→ (fmem.bit)	*4	
		CY, pmem.@L	2	2	CY←CY √ (pmem7-2+L3-2.bit(L1-0))	*5	
		CY, @H+mem.bit	2	2	CY←CY∀(H+mem3-0.bit)	*1	



Instruction Group	Mnemonic	Operand	No. of Bytes	Machine Cycle	Operation	Addressing Area	Skip Condition
Branch BRNote		addr	_	_	PC13-0←addr Use the assembler to select the most appropriate instruction among the following. • BR laddr • BRCB !caddr • BR \$addr	*6	
		addr1	ı	_	PC13-0←addr1 Use the assembler to select the most appropriate instruction among the following. • BRA !addr1 • BR !addr • BRCB !caddr • BR \$addr1	*11	
		!addr	3	3	PC13-0←addr	*6	
		\$addr	1	2	PC13-0←addr	*7	
		\$addr1	1	2	PC13-0←addr1		
		PCDE	2	3	PC13-0←PC13-8+DE		
		PCXA	2	3	PC13-0←PC13-8+XA		
		BCDE	2	3	PC13-0←BCDE	*6	
		BCXA	2	3	PC13-0←BCXA	*6	
	BRA ^{Note}	!addr1	3	3	PC13-0←addr1	*11	
	BRCB	!caddr	2	2	PC13-0←PC13, 12+caddr11-0	*8	

Note Shaded areas indicate support for Mk II mode only. Other areas indicate support for Mk I mode only.



Instruction Group	Mnemonic	Operand	No. of Bytes	Machine Cycle	Operation	Addressing Area	Skip Condition
Subroutine stack control	CALLANote	!addr1	3	3	$(SP-6)(SP-3)(SP-4) \leftarrow PC_{11-0}$ $(SP-5) \leftarrow 0, 0, PC_{13, 12}$ $(SP-2) \leftarrow X, X, MBE, RBE$ $PC_{13-0} \leftarrow addr_1, SP \leftarrow SP-6$		
	CALLNote	!addr	3	3	(SP-4)(SP-1)(SP-2)←PC11-0 (SP-3)←MBE, RBE, PC13, 12 PC13-0←addr, SP←SP-4	*6	
				4	(SP-6)(SP-3)(SP-4)←PC11-0 (SP-5)←0, 0, PC13, 12 (SP-2)←X, X, MBE, RBE PC13-0←addr, SP←SP-6		
	CALLFNote	!faddr	2	2	(SP-4)(SP-1)(SP-2)←PC11-0 (SP-3)←MBE, RBE, PC13, 12 PC13-0←000+faddr, SP←SP-4	*9	
				3	$(SP-6)(SP-3)(SP-4) \leftarrow PC_{11-0}$ $(SP-5) \leftarrow 0, 0, PC_{13, 12}$ $(SP-2) \leftarrow X, X, MBE, RBE$ $PC_{13-0} \leftarrow 000 + faddr, SP \leftarrow SP-6$		
	RETNote		1	3	MBE, RBE, PC ₁₃ , ₁₂ ←(SP+1) PC ₁₁₋₀ ←(SP)(SP+3)(SP+2) SP←SP+4		
					X, X, MBE, RBE←(SP+4) PC11-0←(SP)(SP+3)(SP+2) MBE, 0, PC13, 12←(SP+1) SP←SP+6		
	RETSNote		1	3+S	MBE, RBE, PC13, 12←(SP+1) PC11-0←(SP)(SP+3)(SP+2) SP←SP+4 then skip unconditionally		Unconditional
					X, X, MBE, RBE←(SP+4) PC11-0←(SP)(SP+3)(SP+2) 0, 0, PC13, 12←(SP+1) SP←SP+6 then skip unconditionally		
	RETINote		1	3	MBE, RBE, PC ₁₃ , 12←(SP+1) PC ₁₁₋₀ ←(SP)(SP+3)(SP+2) PSW←(SP+4)(SP+5), SP←SP+6		
					0, 0, PC13, 12←(SP+1) PC11-0←(SP)(SP+3)(SP+2) PSW←(SP+4)(SP+5), SP←SP+6		
	PUSH	rp	1	1	(SP-1)(SP-2)←rp, SP←SP-2		
		BS	2	2	$(SP-1)\leftarrow MBS, (SP-2)\leftarrow RBS, SP\leftarrow SP-2$		
	POP	rp	1	1	rp←(SP+1)(SP), SP←SP+2		
		BS	2	2	$MBS {\leftarrow} (SP+1),RBS {\leftarrow} (SP),SP {\leftarrow} SP+2$		

Note Shaded areas indicate support for Mk II mode only. Other areas indicate support for Mk I mode only.



Instruction Group	Mnemonic	Operand	No. of Bytes	Machine Cycle	Operation	Addressing Area	Skip Condition
Interrupt	EI		2	2	IME(IPS.3)←1		
control		IEXXX	2	2	IEXXX←1		
	DI		2	2	IME(IPS.3)←0		
		IEXXX	2	2	IEXXX←0		
I/O	INNote 1	A, PORTn	2	2	A←PORTn (n=0-3, 5, 6, 8, 9)		
		XA, PORTn	2	2	XA←PORTn+1, PORTn(n=8)		
	OUTNote 1	PORTn, A	2	2	PORTn←A (n=2-3, 5, 6, 8, 9)		
		PORTn, XA	2	2	PORTn+1, PORTn←XA(n=8)		
CPU control	HALT		2	2	Set HALT Mode(PCC.2←1)		
	STOP		2	2	Set STOP Mode(PCC.3←1)		
	NOP		1	1	No Operation		
Special	SEL	RBn	2	2	RBS←n (n=0-3)		
		MBn	2	2	MBS←n (n=0, 1, 15)		
	GETI ^{Note 2, 3}	taddr	1	3	When using TBR instruction	*10	
					PC13-0←(taddr)5-0+(taddr+1)		
					When using TCALL instruction		
					(SP-4)(SP-1)(SP-2)←PC11-0		
					(SP+1)←MBE, RBE, PC13, 12		
					PC13-0←(taddr)5-0+(taddr+1)		
					SP←SP–4		
					When using instruction other than		Determined by
					TBR or TCALL		referenced
					Execute (taddr)(taddr+1) instructions		instruction
			1	3	When using TBR instruction	*10	
					PC13-0←(taddr)5-0+(taddr+1)		
				4	When using TCALL instruction		
					(SP-6)(SP-3)(SP-4)←PC11-0		
					(SP–2)←X, X, MBE, RBE		
					PC13-0←(taddr)5-0+(taddr+1)		
					SP←SP-6		
				3	When using instruction other than		Determined by
					TBR or TCALL		referenced
					Execute (taddr)(taddr+1) instructions		instruction

Notes 1. Before executing the IN or OUT instruction, set MBE to 0 or 1 and set MBE to 15.

- 2. TBR and TCALL instructions are assembler directives for the GETI instruction's table definitions.
- 3. Shaded areas indicate support for Mk II mode only. Other areas indicate support for Mk I mode only.



8. ONE-TIME PROM (PROGRAM MEMORY) WRITE AND VERIFY

The program memory contained in the μ PD75P3216 is a 16384 × 8-bit one-time PROM that can be electrically written one time only. The pins listed in the table below are used for this PROM's write/verify operations. Clock input from the X1 pin is used instead of address input as a method for updating addresses.

Pin	Function
VPP	Pin where program voltage is applied during program memory write/verify (usually VDD potential)
X1, X2	Clock input pins for address updating during program memory write/verify. Input the X1 pin's inverted signal to the X2 pin.
MD0 to MD3	Operation mode selection pin for program memory write/ verify
D0/P60/KR0-D3/P63/KR3 (lower 4 bits) D4/P50-D7/P53 (upper 4 bits)	8-bit data I/O pins for program memory write/verify
VDD	Pin where power supply voltage is applied. Applies 1.8 to 5.5 V in normal operation mode and +6 V for program memory write/verify.

Caution Pins not used for program memory write/verify should be connected to Vss.

8.1 Operation Modes for Program Memory Write/Verify

When +6 V is applied to the V_{DD} pin and +12.5 V to the V_{PP} pin, the μ PD75P3216 enters the program memory write/verify mode. The following operation modes can be specified by setting pins MD0 to MD3 as shown below.

	Operation N	lode Sp	ecificatio	on		Operation Mode
VPP	VDD	MD0	MD1	MD2	MD3	Operation wode
+12.5 V	+6 V	Н	L	Н	L	Zero-clear program memory address
		L	Н	Н	Н	Write mode
		L	L	Н	Н	Verify mode
		Н	Х	Н	Н	Program inhibit mode

X: L or H

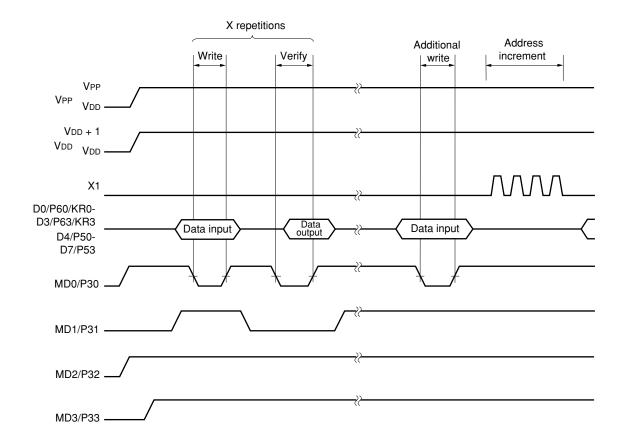


★ 8.2 Program Memory Write Procedure

Program memory can be written at high speed using the following procedure.

- (1) Pull down unused pins to Vss through resistors. Set the X1 pin low.
- (2) Supply 5 V to the VDD and VPP pins.
- (3) Wait 10 μ s.
- (4) Select the zero-clear program memory address mode.
- (5) Supply 6 V to the VDD and 12.5 V to the VPP pins.
- (6) Write data in the 1 ms write mode.
- (7) Select the verify mode. If the data is correct, go to step (8) and if not, repeat steps (6) and (7).
- (8) (X : number of write operations from steps (6) and (7)) \times 1 ms additional write.
- (9) Apply four pulses to the X1 pin to increment the program memory address by one.
- (10) Repeat steps (6) to (9) until the end address is reached.
- (11) Select the zero-clear program memory address mode.
- (12) Return the VDD and VPP pins back to 5 V.
- (13) Turn off the power.

The following figure shows steps (2) to (9).

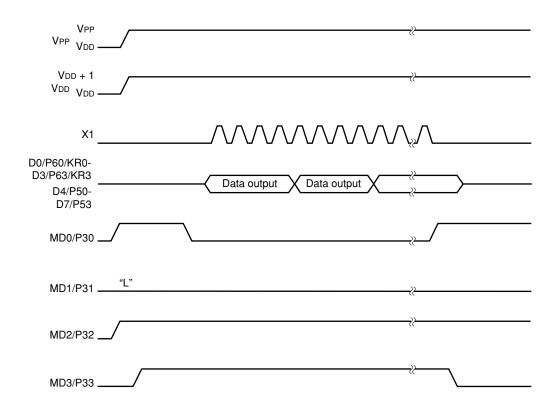


★ 8.3 Program Memory Read Procedure

The μ PD75P3216 can read program memory contents using the following procedure.

- (1) Pull down unused pins to Vss through resistors. Set the X1 pin low.
- (2) Supply 5 V to the VDD and VPP pins.
- (3) Wait 10 μ s.
- (4) Select the zero-clear program memory address mode.
- (5) Supply 6 V to the VDD and 12.5 V to the VPP pins.
- (6) Select the verify mode. Apply four pulses to the X1 pin. Every four clock pulses will output the data stored in one address.
- (7) Select the zero-clear program memory address mode.
- (8) Return the VDD and VPP pins back to 5 V.
- (9) Turn off the power.

The following figure shows steps (2) to (9).



8.4 One-time PROM Screening

Due to its structure, the one-time PROM cannot be fully tested before shipment by NEC Electronics. Therefore, NEC Electronics recommends that after the required data is written and the PROM is stored under the temperature and time conditions shown below, the PROM should be verified via a screening.

Storage Temperature	Storage Time
125 °C	24 hours



***** 9. ELECTRICAL SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C)

Parameter	Symbol		Test Conditions	Rating	Unit
Supply voltage	V _{DD}			-0.3 to +7.0	V
PROM supply voltage	V _{PP}			-0.3 to +13.5	V
Input voltage	VII	Except	port 5	-0.3 to V _{DD} + 0.3	V
	V _{I2}	Port 5	N-ch open-drain	-0.3 to +14	V
Output voltage	Vo			-0.3 to V _{DD} + 0.3	V
Output current, high	Іон	Per pin		-10	mA
		Total fo	r all pins	-30	mA
Output current, low	loL	Per pin		30	mA
		Total fo	r all pins	220	mA
Operating ambient	Та			-40 to +85 ^{Note}	°C
temperature					
Storage temperature	T _{stg}			-65 to +150	°C

Note When LCD is driven in normal mode: $T_A = -10$ to +85 °C

Caution Exposure to Absolute Maximum Ratings even for instant may affect device reliability; exceeding the ratings could cause parmanent damage. The parameters apply independently. The device should be operated within the limits specified under DC and AC Characteristics.

CAPACITANCE (TA = 25 °C, VDD = 0 V)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	Cin	f = 1 MHz			15	pF
Output capacitance	Соит	Unmeasured pins returned to 0 V.			15	pF
I/O capacitance	Сю				15	pF



SYSTEM CLOCK OSCILLATOR CHARACTERISTICS (TA = -40 to +85 °C, VDD = 1.8 to 5.5 V)

Resonator	Recommended Constant	Parameter	Test Conditions	MIN.	TYP.	MAX.	Unit
Ceramic	X1 X2	Oscillator		1.0		6.0 Note 2	MHz
resonator		frequency (fx) Note 1					
	C1 C2	Oscillation	After VDD reaches oscil-			4	ms
	V _{DD}	stabilization time Note 3	lation voltage range MIN.				
Crystal	X1	Oscillator		1.0		6.0 Note 2	MHz
resonator		frequency (fx) Note 1					
	C1 + C2	Oscillation	V _{DD} = 4.5 to 5.5 V			10	ms
	\\-_\ _{VDD}	stabilization time Note 3				30	
External		X1 input		1.0		6.0 Note 2	MHz
clock	X1 X2	frequency (fx) Note 1					
	→ N=	X1 input		83.3		500	ns
	Å	high/low level width					
		(txH, txL)					

- **Notes 1.** The oscillator frequency and X1 input frequency indicate characteristics of the oscillator only. For the instruction execution time, refer to the AC characteristics.
 - 2. When the oscillator frequency is 4.19 MHz < fx \leq 6.0 MHz, setting the processor clock control register (PCC) to 0011 results in 1 machine cycle being less than the required 0.95 μ s. Therefore, set PCC to a value other than 0011.
 - 3. The oscillation stabilization time is necessary for oscillation to stabilize after applying VDD or releasing the STOP mode.

Caution When using the system clock oscillator, wiring in the area enclosed with the dotted line should be carried out as follows to avoid an adverse effect from wiring capacitance.

- · Wiring should be as short as possible.
- · Wiring should not cross other signal lines.
- · Wiring should not be placed close to a varying high current.
- The potential of the oscillator capacitor ground should be the same as Vss.
- Do not ground it to the ground pattern in which a high current flows.
- · Do not fetch a signal from the oscillator.



DC CHARACTERISTICS (TA = -40 to +85 °C, VDD = 1.8 to 5.5 V)

Parameter	Symbol		Test Condition	s	MIN.	TYP.	MAX.	Unit
Output current, low	loL	Per pin					15	mA
		Total for all pins	3				150	mA
Input voltage, high	V _{IH1}	Ports 2, 3, 8, 9		$2.7 \le V_{DD} \le 5.5 \text{ V}$	0.7V _{DD}		V _{DD}	V
		$1.8 \le V_{DD} < 2.7 V$			0.9V _{DD}		V _{DD}	V
	V _{IH2}	Ports 0, 1, 6, R	Ports 0, 1, 6, RESET 2		0.8V _{DD}		V _{DD}	V
				1.8 ≤ V _{DD} < 2.7 V	0.9V _{DD}		V _{DD}	V
	VIH3	Port 5	N-ch open-drain	2.7 ≤ V _{DD} ≤ 5.5 V	0.7V _{DD}		13	V
				1.8 ≤ V _{DD} < 2.7 V	0.9V _{DD}		13	V
	V _{I14}	X1			V _{DD} - 0.1		V _{DD}	V
Input voltage, low	V _{IL1}	Ports 2, 3, 5, 8,	9	2.7 ≤ V _{DD} ≤ 5.5 V	0		0.3V _{DD}	V
				1.8 ≤ V _{DD} < 2.7 V	0		0.1V _{DD}	V
	V _{IL2}	Ports 0, 1, 6, R	ESET	$2.7 \le V_{DD} \le 5.5 \text{ V}$	0		0.2V _{DD}	V
				1.8 ≤ V _{DD} < 2.7 V	0		0.1V _{DD}	V
	V _{IL3}	X1			0		0.1	V
Output voltage, high	Vон	SCK, SO, ports 2, 3, 6, 8, 9 lo _H = −1 mA						V
Output voltage, low	V _{OL1}	SCK, SO, ports	2, 3, 5, 6, 8, 9	loL = 15 mA,		0.2	2.0	V
				V _{DD} = 4.5 to 5.5 V				
				IoL = 1.6 mA			0.4	V
	V _{OL2}	SB0, SB1	N-ch open-drain p	ull-up resistor \ge 1 kΩ			0.2V _{DD}	V
Input leakage	ILIH1	VIN = VDD	Other pins than >	(1			3	μΑ
current, high	ILIH2		X1				20	μΑ
	Ілнз	VIN = 13 V	Port 5 (N-ch oper	n-drain)			20	μΑ
Input leakage	ILIL1	VIN = 0 V	Other pins than p	ort 5 and X1			-3	μΑ
current, low	ILIL2		X1				-20	μΑ
	ILIL3		Port 5 (N-ch oper	n-drain) When an			-3	μΑ
			input instruction i	s not executed				
			Port 5 (N-ch				-30	μΑ
			open-drain)					
			When an input	V _{DD} = 5.0 V		-10	-27	μΑ
			instruction	V _{DD} = 3.0 V		-3	-8	μΑ
			is executed					
Output leakage	Ісон1	Vout = Vdd	SCK, SO/SB0, SE	31, ports 2, 3, 6, 8, 9			3	μΑ
current, high	Ісон2	Vout = 13 V	Port 5 (N-ch oper	n-drain)			20	μΑ
Output leakage	Ісог	$V_{OUT} = 0 V$					-3	μΑ
current, low								
Pull-up resistor	R∟	$V_{IN} = 0 V$	Ports 0, 1, 2, 3, 6	6, 8, 9	50	100	200	kΩ
			(Excluding P00 p	in)				



DC CHARACTERISTICS ($T_A = -40 \text{ to } +85 ^{\circ}\text{C}$, $V_{DD} = 1.8 \text{ to } 5.5 \text{ V}$)

Parameter	Symbol	Test Conditions			MIN.	TYP.	MAX.	Unit
LCD drive voltage	VLCD	VAC0 = 0	$T_A = -40 \text{ to } -$	+85 °C	2.7		V _{DD}	٧
			$T_A = -10 \text{ to } -$	+85 °C	2.2		V _{DD}	٧
		VAC0 = 1			1.8		V _{DD}	V
VAC current	Ivac	VAC0 = 1, VDD = 2.	.0 V ± 10%			1	4	μΑ
LCD output voltage	Vodc	lo = ±1 μA	VLCDO = VLCD		0		±0.2	V
deviation Note 1 (common)			VLCD1 = VLCD	× 2/3				
LCD output voltage	Vods	lo = ±0.5 μA	VLCD2 = VLCD	× 1/3	0		±0.2	V
deviation Note 1 (segment)			2.2 V ≤ VLCD	\leq V_{DD} Note 1				
Supply current Note 2	I _{DD1}	6.0 MHz	$V_{DD} = 5.0 \text{ V} \pm 10\% \text{ Note 3}$			2.6	7.8	mA
	Crystal oscillat	Crystal oscillation	VDD = 3.0 V ± 10% Note 4			0.47	1.4	mA
	I _{DD2}	C1 = C2 = 22 pF	HALT mode	$V_{DD} = 5.0 \text{ V} \pm 10\%$		0.72	2.1	mA
				V _{DD} = 3.0 V ± 10%		0.27	0.8	mA
	I _{DD1}	4.19 MHz	VDD = 5.0 V	± 10% Note 3		1.9	5.7	mA
		Crystal oscillation	V _{DD} = 3.0 V :	± 10% Note 4		0.36	1.1	mA
	I _{DD2}	C1 = C2 = 22 pF	HALT mode	$V_{DD} = 5.0 \text{ V} \pm 10\%$		0.7	2.0	mA
				V _{DD} = 3.0 V ± 10%		0.23	0.7	mA
	I _{DD5}	STOP mode Note 5	VDD = 5.0 V	± 10%		0.05	10	μΑ
			V _{DD} = 3.0 V			0.02	5	μΑ
			±10%	T _A = 25°C		0.02	3	μΑ

Notes 1. The voltage deviation is the difference from the output voltage corresponding to the ideal value of the segment and common outputs (V_{LCDn} ; n = 0, 1, 2).

- 2. Not including current flowing in on-chip pull-up resistors.
- 3. When the processor clock control register (PCC) is set to 0011 and the device is operated in the high-speed mode.
- 4. When PCC is set to 0000 and the device is operated in the low-speed mode.
- 5. Set VAC0 to 0 when setting the STOP mode. If VAC0 is set to 1, the current increases by about 1 μ A.

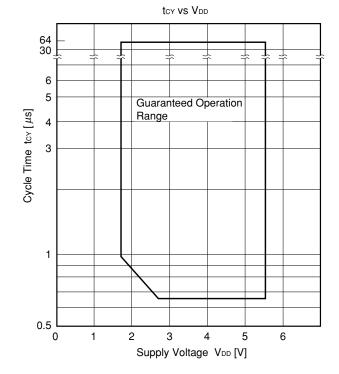
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AC CHARACTERISTICS (Ta = -40 to +85 °C, VDD = 1.8 to 5.5 V)

Parameter	Symbol	Test Conditions			TYP.	MAX.	Unit
CPU clock cycle	tcy	V _{DD} = 2.7 to 5.5 V				64	μs
time Note 1				0.95		64	μs
TI0 input frequency	fтı	V _{DD} = 2.7 to 5.5 V				1	MHz
				0		275	kHz
TI0 input	t тін, t ті∟	V _{DD} = 2.7 to 5.5 V		0.48			μs
high/low-level width				1.8			μs
Interrupt input high/	tinth, tintl	INT0	IM02 = 0	Note 2			μs
low-level width			IM02 = 1	10			μs
		INT4		10			μs
		KR0 to KR3		10			μs
RESET low level width	trsL			10			μs

- Notes 1. The cycle time (minimum instruction execution time) of the CPU clock (Φ) is determined by the oscillation frequency of the connected resonator (and external clock) and the processor clock control register (PCC). The figure at the right indicates the cycle time toy versus supply voltage VDD characteristic.
 - 2. 2tcy or 128/fx is set by setting the interrupt mode register (IM0).





SERIAL TRANSFER OPERATION

2-Wire and 3-Wire Serial I/O Mode (\overline{SCK} ...Internal clock output): (TA = -40 to +85 °C, V_{DD} = 1.8 to 5.5 V)

Parameter	Symbol	Test Con	MIN.	TYP.	MAX.	Unit	
SCK cycle time	tkcy1	V _{DD} = 2.7 to 5.5 V	1300			ns	
			3800			ns	
SCK high/low-level	tkl1, tkH1	V _{DD} = 2.7 to 5.5 V	tксү1/2-50			ns	
width			tксу1/2-150			ns	
SI ^{Note 1} setup time	tsiĸ1	V _{DD} = 2.7 to 5.5 V	150			ns	
(to SCK↑)			500			ns	
SI ^{Note 1} hold time	t _{KSI1}	V _{DD} = 2.7 to 5.5 V		400			ns
(from SCK↑)				600			ns
SO ^{Note 1} output delay time	tkso1	$R_L = 1 k\Omega$,	V _{DD} = 2.7 to 5.5 V	0		250	ns
from SCK↓		C _L = 100 pF Note 2		0		1000	ns

Notes 1. In the 2-wire serial I/O mode, read SB0 or SB1 instead.

2. RL and CL are the load resistance and load capacitance of the SO output lines.

2-Wire and 3-Wire Serial I/O Mode (SCK...External clock input): (TA = -40 to +85 °C, VDD = 1.8 to 5.5 V)

		-	. , .				
Parameter	Symbol	Test Con	MIN.	TYP.	MAX.	Unit	
SCK cycle time	tkcy2	V _{DD} = 2.7 to 5.5 V	800			ns	
				3200			ns
SCK high/low-level	tkl2, tkH2	V _{DD} = 2.7 to 5.5 V		400			ns
width				1600			ns
SI ^{Note 1} setup time	tsik2	V _{DD} = 2.7 to 5.5 V		100			ns
(to SCK↑)				150			ns
SI ^{Note 1} hold time	tksi2	V _{DD} = 2.7 to 5.5 V		400			ns
(from SCK↑)				600			ns
SO ^{Note 1} output delay time	t KSO2	$R_L = 1 k\Omega$,	V _{DD} = 2.7 to 5.5 V	0		300	ns
from SCK↓		C _L = 100 pF Note 2		0		1000	ns

Notes 1. In the 2-wire serial I/O mode, read SB0 or SB1 instead.

2. RL and CL are the load resistance and load capacitance of the SO output lines.



SBI Mode (SCK...Internal clock output (master)): (TA = -40 to +85 °C, VDD = 1.8 to 5.5 V)

Parameter	Symbol	Test Con	ditions	MIN.	TYP.	MAX.	Unit
SCK cycle time	tксүз	V _{DD} = 2.7 to 5.5 V		1300			ns
				3800			ns
SCK high/low-level	tкьз, tкнз	V _{DD} = 2.7 to 5.5 V		tксүз/2-50			ns
width				tксүз/2-150			ns
SB0, 1 setup time	tsik3	V _{DD} = 2.7 to 5.5 V		150			ns
(to SCK↑)				500			ns
SB0, 1 hold time (from \$\overline{SCK}\bigcap)	tksi3	V _{DD} = 2.7 to 5.5 V		tксүз/2			ns
SB0, 1 output delay	tks03	$R_L = 1 k\Omega$, Note	V _{DD} = 2.7 to 5.5 V	0		250	ns
time from SCK↓		C _L = 100 pF		0		1000	ns
SB0, 1↓ from SCK↑	tĸsв			tĸcʏз			ns
SCK↓ from SB0, 1↑	t sbk			tĸcʏз			ns
SB0, 1 low-level width	tsbl			tксүз			ns
SB0, 1 high-level width	tsвн			tксүз			ns

Note RL and CL are the load resistance and load capacitance of the SB0 and SB1 output lines.

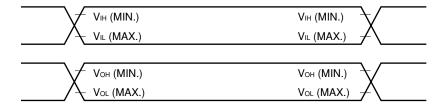
SBI Mode (\overline{SCK} ...External clock input (slave)): (TA = -40 to +85 °C, VDD = 1.8 to 5.5 V)

Parameter	Symbol	Test Con	ditions	MIN.	TYP.	MAX.	Unit
SCK cycle time	tkcy4	V _{DD} = 2.7 to 5.5 V		800			ns
				3200			ns
SCK high/low-level	tkl4, tkH4	V _{DD} = 2.7 to 5.5 V		400			ns
width				1600			ns
SB0, 1 setup time	tsik4	V _{DD} = 2.7 to 5.5 V		100			ns
(to SCK ↑)				150			ns
SB0, 1 hold time (from SCK↑)	t _{KSI4}	V _{DD} = 2.7 to 5.5 V		tkcy4/2			ns
SB0, 1 output delay	tkso4	$R_L = 1 \text{ k}\Omega,^{\text{Note}}$	V _{DD} = 2.7 to 5.5 V	0		300	ns
time from SCK↓		C _L = 100 pF		0		1000	ns
SB0, 1↓ from SCK↑	tĸsв			tkcy4			ns
SCK↓ from SB0, 1↑	tsвк			tkcy4			ns
SB0, 1 low-level width	tsbl			tkcy4			ns
SB0, 1 high-level width	tsвн			tkcy4			ns

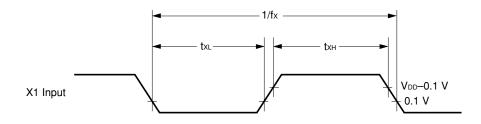
 $\textbf{Note} \quad \text{RL and CL are the load resistance and load capacitance of the SB0 and SB1 output lines}.$



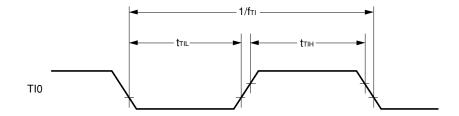
AC Timing Test Point (Excluding X1 Input)



Clock Timing



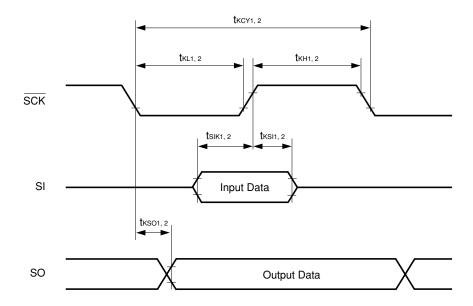
TIO Timing



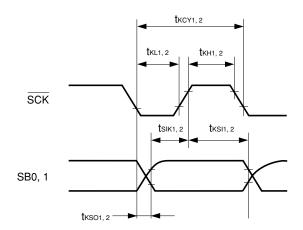


Serial Transfer Timing

3-wire serial I/O mode



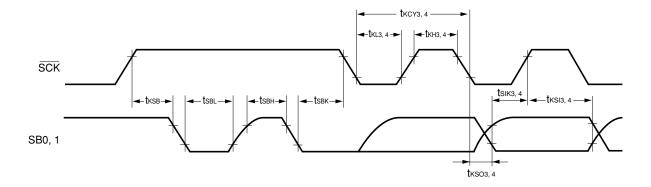
2-wire serial I/O mode



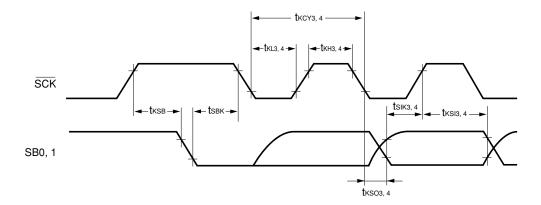


Serial Transfer Timing

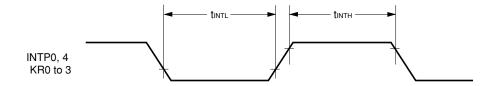
Bus release signal transfer



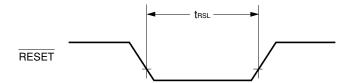
Command signal transfer



Interrupt input timing



RESET input timing





DATA MEMORY STOP MODE LOW SUPPLY VOLTAGE DATA RETENTION CHARACTERISTICS

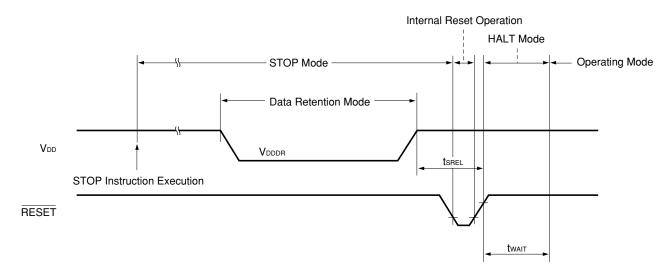
 $(T_A = -40 \text{ to } +85 \text{ }^{\circ}\text{C})$

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Release signal set time	tsrel		0			μs
Oscillation stabilization	twait	Release by RESET		215/fx		ms
wait time Note 1		Release by interrupt		Note 2		ms

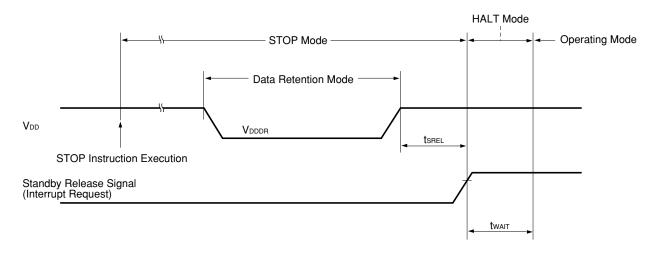
- **Notes 1.** The oscillation stabillization wait time is the time during which the CPU operation is stopped to prevent unstable operation at the oscillation start.
 - 2. Depends on the basic interval timer mode register (BTM) settings (See the table below).

втмз	BTM2	BTM1	BTM0	Wait Time		
				When fx = 4.19-MHz operation	When fx = 6.0-MHz operation	
_	0	0	0	2 ²⁰ /fx (approx. 250 ms)	2 ²⁰ /fx (approx. 175 ms)	
_	0	1	1	2 ¹⁷ /fx (approx. 31.3 ms)	2 ¹⁷ /fx (approx. 21.8 ms)	
_	1	0	1	2 ¹⁵ /fx (approx. 7.81 ms)	2 ¹⁵ /fx (approx. 5.46 ms)	
_	1	1	1	2 ¹³ /fx (approx. 1.95 ms)	2 ¹³ /fx (approx. 1.37 ms)	

Data Retention Timing (STOP Mode Release by RESET)



Data Retention Timing (Standby Release Signal: STOP Mode Release by Interrupt Signal)





DC Programming Characteristics (TA = 25 \pm 5 °C, VDD = 6.0 \pm 0.25 V, VPP = 12.5 \pm 0.3 V, Vss = 0V)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	Other than X1, X2 pins	0.7 V _{DD}		V _{DD}	V
	V _{IH2}	X1, X2	V _{DD} - 0.5		V _{DD}	V
Input voltage, low	V _{IL1}	Other than X1, X2 pins	0		0.3 V _{DD}	V
	V _{IL2}	X1, X2	0		0.4	V
Input leakage current	lu	VIN = VIL OF VIH			10	μ A
Output voltage, high	Vон	lон = − 1 mA	V _{DD} - 1.0			V
Output voltage, low	Vol	IoL = 1.6 mA			0.4	V
V _{DD} supply current	IDD				30	mA
VPP supply current	IPP	MD0 = VIL, MD1 = VIH			30	mA

Cautions 1. Keep VPP to within +13.5 V, including overshoot.

2. Apply VDD before VPP and turn it off after VPP.

AC Programming Characteristics (T_A = 25 \pm 5 °C, V_{DD} = 6.0 \pm 0.25 V, V_{PP} = 12.5 \pm 0.3 V, V_{SS} = 0 V)

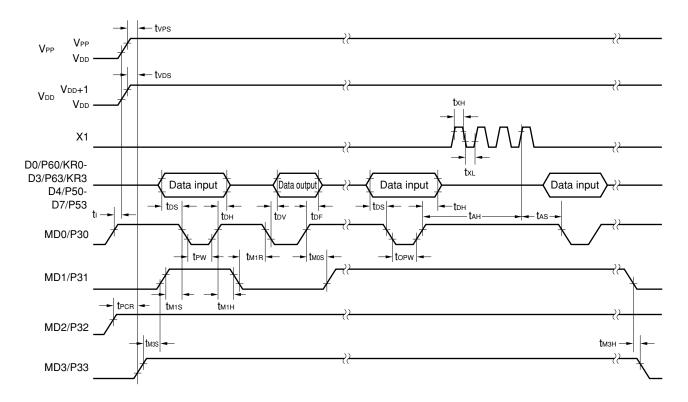
Parameter	Symbol	Note 1	Test Conditions	MIN.	TYP.	MAX.	Unit
Address setup time Note 2 (vs. MD0 ↓)	t as	tas		2			μs
MD1 setup time (vs. MD0 ↓)	t _{M1S}	toes		2			μs
Data setup time (vs. MD0 ↓)	tos	tos		2			μs
Address hold time Note 2 (vs. MD0 ↑)	tан	tah		2			μs
Data hold time (vs. MD0 ↑)	t DH	tон		2			μs
MD0 $\uparrow \rightarrow$ data output float delay time	t DF	tof		0		130	ns
V _{PP} setup time (vs. MD3 ↑)	tvps	tvps		2			μs
V _{DD} setup time (vs. MD3 ↑)	tvos	tvcs		2			μs
Initial program pulse width	tpw	tpw		0.95	1.0	1.05	ms
Additional program pulse width	topw	topw		0.95		21.0	ms
MD0 setup time (vs. MD1 ↑)	tмos	tces		2			μs
MD0 \downarrow \rightarrow data output delay time	tov	tov	MD0 = MD1 = VIL			1	μs
MD1 hold time (vs. MD0 ↑)	t _{м1} н	toeh	tм1H + tM1R ≥ 50 μs	2			μs
MD1 recovery time (vs. MD0 ↓)	t _{M1R}	tor		2			μs
Program counter reset time	tpcr	_		10			μs
X1 input high-, low-level width	tхн, tхL	_		0.125			μs
X1 input frequency	fx	_				4.19	MHz
Initial mode set time	t ₁	_		2			μs
MD3 setup time (vs. MD1 ↑)	tмзs	_		2			μs
MD3 hold time (vs. MD1 ↓)	tмзн	_		2			μs
MD3 setup time (vs. MD0 ↓)	tмзsп	_	When program memory is read	2			μs
Address Note 2 \rightarrow data output delay time	t dad	tacc	When program memory is read			2	μs
Address Note 2 \rightarrow data output hold time	t HAD	tон	When program memory is read	0		130	ns
MD3 hold time (vs. MD0 ↑)	tмзня	_	When program memory is read	2			μs
MD3 $\downarrow \rightarrow$ data output float delay time	t DFR	_	When program memory is read			2	μs

Notes 1. Symbol of corresponding μ PD27C256A

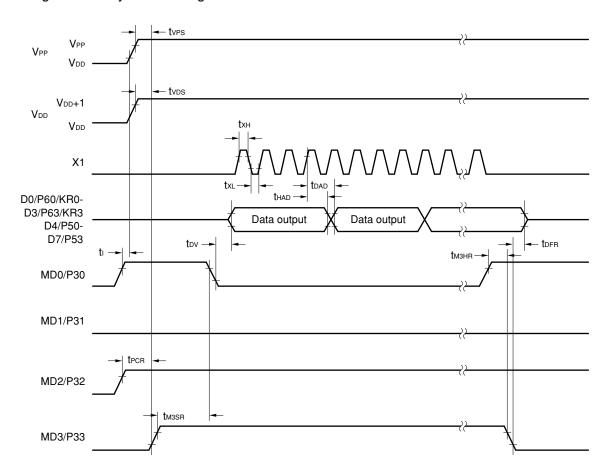
2. The internal address signal is incremented by one at the rising edge of the fourth X1 input and is not connected to a pin.



Program Memory Write Timing

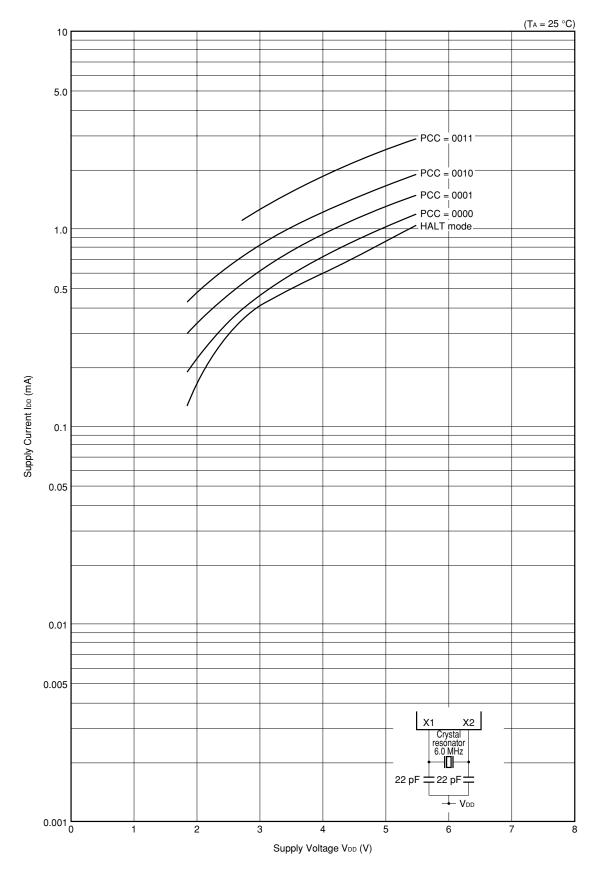


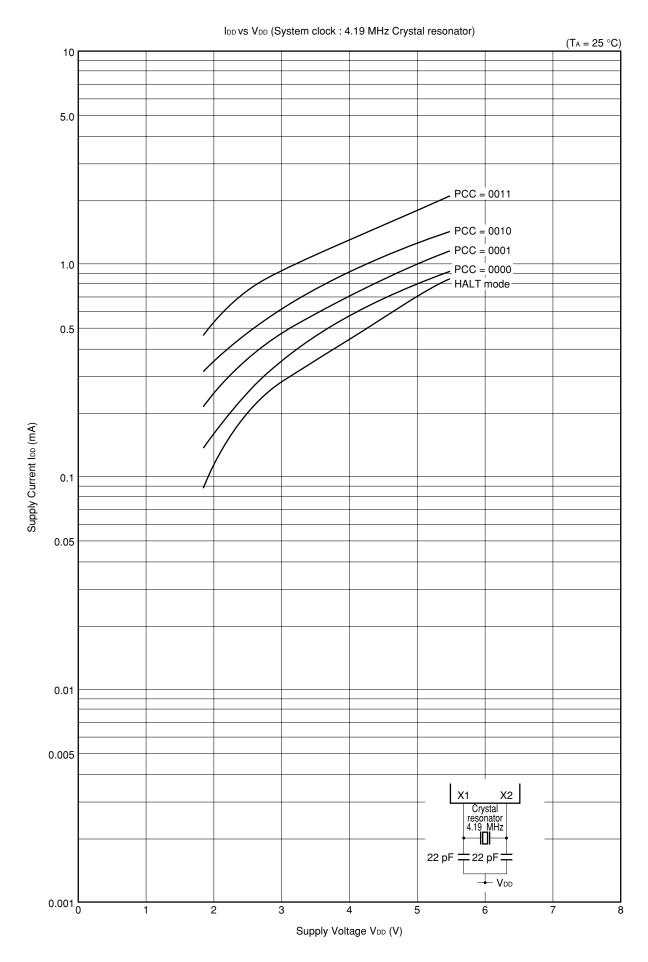
Program Memory Read Timing



★ 10. CHARACTERISTIC CURVE (REFERENCE VALUE)

IDD vs VDD (System clock : 6.0 MHz Crystal resonator)

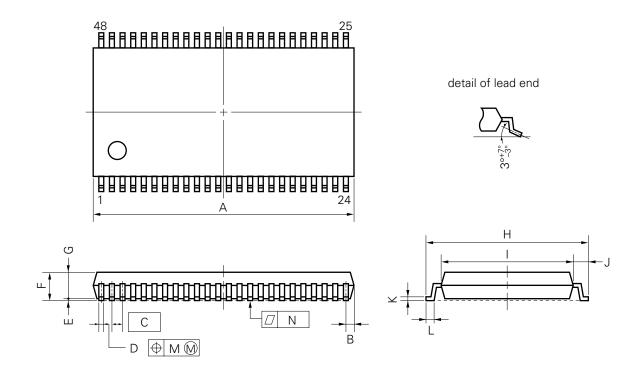






11. PACKAGE DRAWINGS

48 PIN PLASTIC SHRINK SOP (375 mil)



NOTE

Each lead centerline is located within 0.10 mm (0.004 inch) of its true position (T.P.) at maximum material condition.

P48GT-65-375B-1

ITEM	MILLIMETERS	INCHES
А	16.21 MAX.	0.639 MAX.
В	0.63 MAX.	0.025 MAX.
С	0.65 (T.P.)	0.026 (T.P.)
D	0.30±0.10	$0.012^{+0.004}_{-0.005}$
Е	0.125±0.075	0.005±0.003
F	2.0 MAX.	0.079 MAX.
G	1.7±0.1	0.067±0.004
Н	10.0±0.3	$0.394^{+0.012}_{-0.013}$
1	8.0±0.2	0.315±0.008
J	1.0±0.2	$0.039^{+0.009}_{-0.008}$
K	$0.15^{+0.10}_{-0.05}$	$0.006^{+0.004}_{-0.002}$
L	0.5±0.2	$0.020^{+0.008}_{-0.009}$
М	0.10	0.004
N	0.10	0.004

★ 12. RECOMMENDED SOLDERING CONDITIONS

The μ PD75P3216 should be soldered and mounted under the following recommended conditions. For technical information, see the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

Table 12-1. Surface Mounting Type Soldering Conditions

(1) μ PD75P3216GT: 48-pin plastic shrink SOP (375 mil, 0.65 mm pitch)

Soldering Method	Soldering Conditions	Recommended
		Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher),	IR35-107-2
	Count: Twice or less,	
	Exposure limit: 7 days ^{Note} (after that, prebake at 125°C for 10 to 72 hours)	
VPS	Package peak temperature: 215°C, Time: 40 seconds max. (at 200°C or higher),	VP15-107-2
	Count: Twice or less,	
	Exposure limit: 7 days ^{Note} (after that, prebake at 125°C for 10 to 72 hours)	
Wave soldering	Solder bath temperature: 260°C max., Time: 10 seconds max., Count: Once	WS60-107-1
	Preheating temperature: 120°C max. (package surface temperature)	
	Exposure limit: 7 days ^{Note} (after that, prebake at 125°C for 10 to 72 hours)	
Partial heating	Pin temperature: 350°C max., Time: 3 seconds max. (per pin row)	_

Note After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

Remark For soldering methods and conditions other than those recommended above, contact an NEC Electronics sales representative.

\star (2) μ PD75P3216GT-A: 48-pin plastic shrink SOP (375 mil, 0.65 mm pitch)

Undefined

Remark Products with "-A" at the end of the part number are lead-free products.



\star APPENDIX A. μ PD753108, 753208, AND 75P3216 FUNCTIONAL LIST

	Parameter	μPD753108	μPD753208	μPD75P3216		
Program memory		0000H-	ROM -1FFFH < 8 bits)	One-time PROM 0000H-3FFFH (16384 × 8 bits)		
Data memor	ry		000H-1FFH (512 × 4 bits)	1		
CPU			75XL CPU			
Instruction execution	When main system clock is selected	• 0.95, 1.91, 3.81, 15.3 μs (@ • 0.67, 1.33, 2.67, 10.7 μs (@	'			
time	When subsystem clock is selected	122 μs (@ 32.768-kHz operation)	None			
I/O port	CMOS input	8 (on-chip pull-up resistors can be specified by software: 7)	6 (on-chip pull-up resistors can	be specified by software: 5)		
	CMOS input/output	20 (on-chip pull-up resistors ca	in be specified by software)			
	N-ch open drain input/output	4 (on-chip pull-up resistors can withstand voltage is 13 V)	be specified by software,	4 (no mask option, withstand voltage is 13 V)		
	Total	32	30			
LCD control	ler/driver	Segment selection: 16/20/24 (can be changed to CMOS input/output port in 4 time-unit; max. 8)	Segment selection: 4/8/12 segments (can be changed to CMOS input/output port in 4 time-unit max. 8)			
		Display mode selection: static, 1/4 duty (1/3 bias)	Display mode selection: static, 1/2 duty (1/2 bias), 1/3 duty (1/2 bias), 1/3 duty (1/3 bias), 1/4 duty (1/3 bias)			
		On-chip split resistor for LCD dusing mask option.	driver can be specified by No on-chip split re LCD driver			
Timer		5 channels • 8-bit timer/event counter: 3 channels (Can be used as 16-bit timer/event counter, carrier generator, timer with gate) • Basic interval timer/ watchdog timer: 1 channel • Watch timer: 1 channel	5 channels • 8-bit timer counter: 2 channels (Can be used as 16-bit timer counter, carrier generator, timer with gate) • 8-bit timer/event counter: 1 channel • Basic interval timer/watchdog timer: 1 channel • Watch timer: 1 channel			
Clock output	t (PCL)	 Φ, 524, 262, 65.5 kHz (Main system clock: @ 4.19-I Φ, 750, 375, 93.8 kHz (Main system clock: @ 6.0-M 				
Buzzer output (BUZ)		2, 4, 32 kHz (Main system clock: @ 4.19-MHz operation or subsystem clock: @ 32.768-kHz operation) 2.86, 5.72, 45.8 kHz (Main system clock: @ 6.0-MHz operation)	2, 4, 32 kHz (Main system clock: @ 4.19-MHz operation) 2.93, 5.86, 46.9 kHz			
Serial interfa	ace	3 modes are available 3-wire serial I/O mode MSE 2-wire serial I/O mode SBI mode	B/LSB can be selected for transfer	top bit		
SCC registe	r	Contained	None			
			l .			
SOS registe	r					



Parameter	μPD753108	μPD753208	μPD75P3216			
Test input	External: 1, internal: 1					
Operation supply voltage	V _{DD} = 1.8 to 5.5 V					
Operating ambient temperature	$T_A = -40 \text{ to } +85^{\circ}\text{C}$					
Package	64-pin plastic QFP (14 × 14 mm) 64-pin plastic QFP (12 × 12 mm) 48-pin plastic shrink SOP (375 mil, 0.65-mm pitch)					



APPENDIX B. DEVELOPMENT TOOLS

The following development tools have been provided for system development using the μ PD75P3216. In the 75XL series, relocatable assemblers common to the series can be used in combination with the device files for each product type.

RA75X relocatable assembler	Host machine	Part No. (name)		
		OS	Supply medium	
	PC-9800 Series	MS-DOS™	3.5" 2HD	μS5A13RA75X
		(Ver.3.30 to	5" 2HD	μS5A10RA75X
		Ver.6.2Note		
	IBM PC/AT™	Refer to "OS for	3.5" 2HC	μS7B13RA75X
	or compatible	IBM PCs"	5" 2HC	μS7B10RA75X

Device file	Host machine	Part No. (name)		
		os	Supply medium	
	PC-9800 Series	MS-DOS™	3.5" 2HD	μS5A13DF753208
		Ver.3.30 to	5" 2HD	μS5A10DF753208
		Ver.6.2Note		
	IBM PC/AT	Refer to "OS for	3.5" 2HC	μS7B13DF753208
	or compatible	IBM PCs"	5" 2HC	μS7B10DF753208

Note Ver. 5.00 or later includes a task swapping function, but this software is not able to use that function.

Remark Operation of the PG-1500 controller is guaranteed only when using the host machine and OS described above.



PROM Write Tools

Hardware	PG-1500	This is a PROM programmer that can program single-chip microcomputer with PROM in stand alone mode or under control of host machine when connected with supplied accessory board and optional programmer adapter. It can also program typical PROMs in capacities ranging from 256 K to 4 M bits. This is a PROM programmer adapter for the µPD75P3216GT. It can be used when connected to a PG-1500.			
	PA-75P3216GT				
Software	PG-1500 controller	Connects PG-1500 to host machine with serial and parallel interface and controls PG-1500 on host machine.			
		Host machine Part No. (nam			Part No. (name)
			os	Supply medium	
		PC-9800 Series	MS-DOS	3.5" 2HD	μS5A13PG1500
			Ver.3.30 to Ver.6.2 ^{Note}	5" 2HD	μS5A10PG1500
		IBM PC/AT	Refer to "OS for	3.5" 2HD	μS7B13PG1500
		or compatible	IBM PCs"	5" 2HC	μS7B10PG1500

Note Ver. 5.00 or later includes a task swapping function, but this software is not able to use that function.

Remark Operation of the PG-1500 controller is guaranteed only when using the host machine and OS described above.



Debugging Tools

In-circuit emulators (IE-75000-R and IE-75001-R) are provided as program debugging tools for the μ PD75P3216. Various system configurations using these in-circuit emulators are listed below.

Hardware	Hardware IE-75000-R ^{Note 1} The IE-75000-R is an in-circuit emulator to be used for hardware and soft during development of application systems using the 75X or 75XL Series For development of the μPD753208 subseries, the IE-75000-R is used with emulation board (IE-75300-R-EM) and emulation probe (EP-753208GT-R) Highly efficient debugging can be performed when connected to host mac programmer. The IE-75000-R includes a connected emulation board (IE-75000-R-EM).				es products. I with optional I-R). nachine and PROM
	IE-75001-R	The IE-75001-R is an in-circuit emulator to be used for hardware and software debugging during development of application systems using the 75X or 75XL Series products. The IE-75001-R is used in combination with optional emulation board (IE-75300-R-EM) and emulation probe (EP-753208GT-R). Highly efficient debugging can be performed when connected to host machine and PROM programmer.			
	IE-75300-R-EM	This is an emulation board for evaluating application systems using the μ PD75P3216. It is used in combination with the IE-75000-R or IE-75001-R.			
	EP-753208GT-R	This is an emulation probe for the μ PD75P3216GK. When being used, it is connected with the IE-75000-R or IE-75001-R and the IE-75300-R-EM.			
	EV-9500GT-48	It includes a flexible bo	oard (EV-9500GT-48) to	facilitate connections wi	th target system.
Software	IE control program	This program can control the IE-75000-R or IE-75001-R on a host machine when connected to the IE-75000-R or IE-75001-R via an RS-232-C or Centronics interface.			
		Host machine			Part No. (name)
			os	Supply medium	
		PC-9800 Series	MS-DOS	3.5" 2HD	μS5A13IE75X
			Ver.3.30 to Ver.6.2 ^{Note 2}	5" 2HD	μS5A10IE75X
		IBM PC/AT	Refer to "OS for	3.5" 2HC	μS7B13IE75X
		or compatible	IBM PCs"	5" 2HC	μS7B10IE75X

- **Notes 1.** This is a maintenance product.
 - **2.** Ver. 5.00 or later includes a task swapping function, but this software is not able to use that function.
- **Remarks 1.** Operation of the IE control program is guaranteed only when using the host machine and OS described above.
 - **2.** The generic name for the μ PD753204, 753206, 753208, and 75P3216 is the μ PD753208 subseries.

OS for IBM PCs

The following operating systems for the IBM PC are supported.

os	Version
PC DOS™	Ver.5.02 to Ver.6.3 J6.1/V ^{Note} to J6.3/V ^{Note}
MS-DOS	Ver.5.0 to Ver.6.22 5.0/V ^{Note} to 6.2/V ^{Note}
IBM DOS™	J5.02/V ^{Note}

Note Only English version is supported.

Caution Ver. 5.0 or later include a task swapping function, but this software is not able to use that function.



APPENDIX C. RELATED DOCUMENTS

Some of the related documents are preliminary but are not marked as such.

Device related documents

Document Name	Document Number	
250amon Namo	Japanese	English
μPD753204, 753206, 753208 preliminary product information	U10166J	U10166E
μPD75P3216 data sheet	U10241J	This document
μPD753208 user's manual	U10158J	U10158E
75XL series selection guide	U10453J	U10453E

Development tool related documents

Document Name			Document Number	
			Japanese	English
Hardware	rdware IE-75000-R/IE-75001-R user's manual IE-75300-R-EM user's manual		EEU-846	EEU-1416
			U11354J	U11354E
	EP-753208GT-R user's manual		U10739J	U10739E
	PG-1500 user's manual		EEU-651	EEU-1335
Software	RA75X assembler package user's manual	Operation	EEU-731	EEU-1346
		Language	EEU-730	EEU-1363
	PG-1500 controller user's manual	PC-9800 series (MS-DOS) base	EEU-704	EEU-1291
		IBM PC series (PC DOS) base	EEU-5008	U10540E

Other related documents

Document Name	Document Number	
250amon Namo	Japanese	English
IC package manual C1094		
Semiconductor device mounting technology manual	C10535J	C10535E
Quality grade on NEC semiconductor devices	C11531J	C11531E
NEC semiconductor device reliability/quality control system	C10983J	C10983E
Static electricity discharge (ESD) test	MEM-539	_
Semiconductor device quality guarantee guide	MEI-603	MEI-1202
Microcomputer related product guide - other manufacturers	U11416J	_

Caution The related documents listed above are subject to change without notice. Be sure to use the latest documents for designing, etc.



NOTES FOR CMOS DEVICES -

1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between $V_{\rm IL}$ (MAX) and $V_{\rm IH}$ (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between $V_{\rm IL}$ (MAX) and $V_{\rm IH}$ (MIN).

(2) HANDLING OF UNUSED INPUT PINS

Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

③ PRECAUTION AGAINST ESD

A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION

Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE

In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current.

The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE

Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.



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- Development environment specifications (for example, specifications for third-party tools and components, host computers, power plugs, AC supply voltages, and so forth)
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